

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	16	MEMS and (getter or titanium) and cavity and cover and substrate and (vacuum near chamber) and inject\$4 and "inert gas" and bond	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/13 09:10
L2	10	MEMS and (getter or titanium) and cavity and cover and substrate and (vacuum near chamber) and inject\$4 and "inert gas" and bond and argon and time and degree	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/13 09:10
L3	3	MEMS and (getter or titanium) and cavity and cover and substrate and (vacuum near chamber) and inject\$4 and "inert gas" and bond and argon and time and degree and anodic	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/13 09:11
L4	7	MEMS and (getter or titanium) and cavity and cover and substrate and (vacuum near chamber) and inject\$4 and argon and time and degree and anodic	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/13 09:12
L5	7	MEMS and (getter or titanium) and cavity and cover and substrate and (vacuum near chamber) and inject\$4 and argon and degree and anodic	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/13 09:12
L6	14	MEMS and (getter or titanium) and cavity and cover and substrate and (vacuum near chamber) and inject\$4 and argon and degree	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/13 09:13
L7	14	MEMS and (getter or titanium) and cavity and cover and substrate and (vacuum near chamber) and inject\$4 and argon and degree and bond	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/13 09:17
L8	7	MEMS and titanium and cavity and cover and (substrate or semiconductor or wafer) and "vacuum chamber" and argon and degree and anodic	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/13 09:24

L9	16970	getter	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/13 09:25
L10	216	(getter near titanium)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/13 09:26
L11	0	(getter near titanium) and cavity and cover and (substrate or semiconductor or wafer) and "vacuum chamber" and degree and bond	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/13 09:29
L12	0	(getter near titanium) and cavity and cover and (substrate or semiconductor or wafer) and (vacuum near chamber) and degree and bond	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/13 09:29
L13	3	(getter near titanium) and cavity and cover and (substrate or semiconductor or wafer)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/13 09:31
L14	0	(getter near titanium) and cavity and cover and (substrate or semiconductor or wafer) and "vacuum chamber"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/13 09:31
L15	0	(getter near titanium) and cavity and cover and (substrate or semiconductor or wafer) and (vacuum near chamber)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/13 09:32
L16	2	(getter near titanium) and cavity and cover and (substrate or semiconductor or wafer) and vacuum	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/13 09:32

L17	2	(getter near titanium) and cavity and cover and (substrate or semiconductor or wafer) and vacuum and chamber	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/13 09:32
L18	1	(getter near titanium) and cavity and cover and (substrate or semiconductor or wafer) and vacuum and chamber and argon	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/13 09:32
L19	0	(getter near titanium) and cavity and cover and (substrate or semiconductor or wafer) and vacuum and chamber and argon and degree	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/13 09:32
L20	0	(getter near titanium) and cavity and cover and (substrate or semiconductor or wafer) and vacuum and chamber and argon and (bond or attach)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/13 09:33
L21	1	(getter near titanium) and cavity and cover and (substrate or semiconductor or wafer) and vacuum and chamber and argon	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/13 10:12
L22	0	(getter near titanium) and (cover near glass) and "anodic bond"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/13 10:13
L23	0	getter near glass and "anodic bond"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/13 10:13
L24	220	"anodic bond"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/13 10:13

L25	9	"anodic bond" and getter	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/13 10:14
L26	6	"anodic bond" and getter and glass	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/13 10:14
L27	6	"anodic bond" and getter and glass and cover	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/13 10:14
L28	6	"anodic bond" and getter and glass and cover and substrate	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/13 10:15
S1	9	MEMS and getter and cavity and cover and (substrate or wafer or semiconductor) and chamber and vacuum and "inert gas" and (temperature or heat or degree) and bond\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/29 12:28
S2	109	getter and cavity and cover and (substrate or wafer or semiconductor) and chamber and vacuum and "inert gas" and (temperature or heat or degree) and bond\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/23 14:47
S3	1	getter and cavity and cover and (substrate or wafer or semiconductor) and chamber and vacuum and "inert gas" and (temperature or heat or degree) and bond\$4 and titanium and time and argon and discharg\$4 and anodic	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/23 14:48
S4	25	getter and cavity and cover and (substrate or wafer or semiconductor) and chamber and vacuum and "inert gas" and (temperature or heat or degree) and bond\$4 and titanium and time and argon	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/23 14:48

S5	144	adhes\$4 and conduct\$4 and binder and filler and (heat\$4 or thermal or temperature) and pressuriz\$4 and viscosity and connect and (hard\$4 or solid)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/13 09:08
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